

# SCHOTTKY BARRIER DIODES

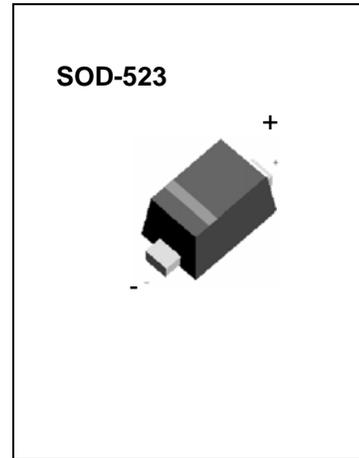
## PRODUCT SUMMARY

SOD-523 Plastic-Encapsulate Diodes

## FEATURES

Small surface mounting type  
 Low  $I_R$ . ( $I_R = 0.1 \mu A$ )  
 High reliability

 **Pb-free; RoHS-compliant**



## MARKING: B

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Single Diode @ $T_A=25^\circ C$

Parameter	Symbol	Limits	Unit
DC reverse voltage	$V_R$	30	V
Mean rectifying current	$I_o$	200	mA
Peak forward surge current	$I_{FSM}$	1	A
Junction temperature	$T_j$	125	$^\circ C$
Storage temperature	$T_{stg}$	-40-125	$^\circ C$

## ELECTRICAL RATINGS @ $T_A=25^\circ C$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$			0.6	V	$I_F=200mA$
Reverse current	$I_R$			1	$\mu A$	$V_R=10V$

## TYPICAL CHARACTERISTICS

● Electrical characteristic curves (Ta=25°C)

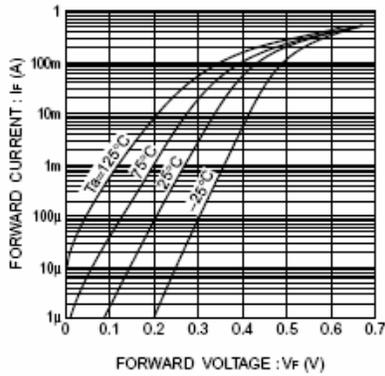


Fig. 1 Forward characteristics

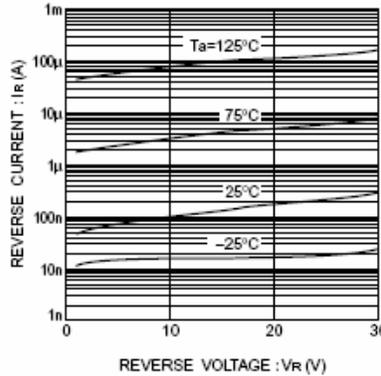


Fig. 2 Reverse characteristics

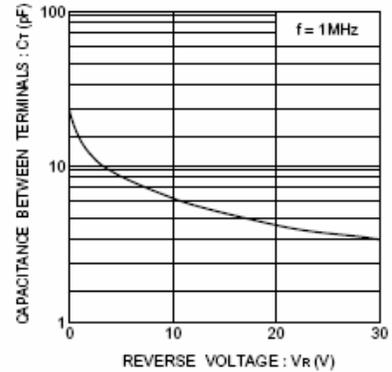


Fig. 3 Capacitance between terminals characteristics

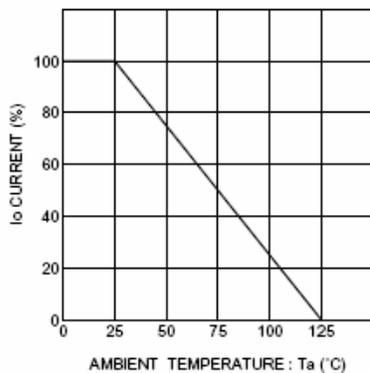


Fig 4. Derating curve  
(mounting on glass epoxy PCBs)

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